

NCE N-Channel Enhancement Mode Power MOSFET

Description

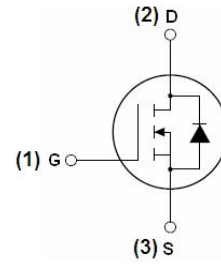
The NCE0275T uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in automotive applications and a wide variety of other applications.

General Features

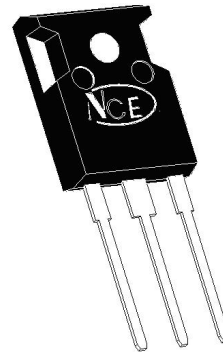
- $V_{DSS} = 200V, I_D = 75A$
 $R_{DS(ON)} < 22m\Omega @ V_{GS} = 10V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Automotive applications
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram



TO-247-3L top view

100% UIS TESTED!
100% ΔV_{ds} TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE0275T	NCE0275T	TO-247-3L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DSS}	200	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	75	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	53	A
Pulsed Drain Current (Note 1)	I_{DM}	300	A
Maximum Power Dissipation	P_D	360	W
Derating factor		2.4	W/ $^\circ C$
Single pulse avalanche energy (Note 3)	E_{AS}	600	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 1)	$R_{\theta JC}$	0.42	$^\circ C/W$
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Electrical Characteristics (T_c=25°C unless otherwise noted)

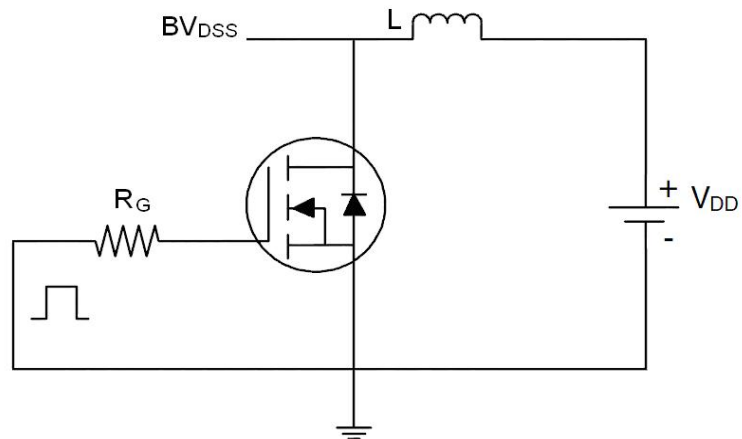
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	200	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =200V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =40A	-	19	22	mΩ
Forward Transconductance	g _{FS}	V _{DS} =20V,I _D =40A	-	115	-	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =100V,V _{GS} =0V, F=1.0MHz	-	8238	-	PF
Output Capacitance	C _{oss}		-	275	-	PF
Reverse Transfer Capacitance	C _{rss}		-	112	-	PF
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =100V,I _D =40A, V _{GS} =10V,R _G =2.7Ω	-	17	-	nS
Turn-on Rise Time	t _r		-	18	-	nS
Turn-Off Delay Time	t _{d(off)}		-	56	-	nS
Turn-Off Fall Time	t _f		-	22	-	nS
Total Gate Charge	Q _g	ID=40A,VDD=100V,VGS=10V	-	152.7	-	nC
Gate-Source Charge	Q _{gs}		-	44.5	-	nC
Gate-Drain Charge	Q _{gd}		-	47.9	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =75A	-	-	1.2	V
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 40A	-	136	-	nS
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs ^(Note2)	-	458	-	nC

Notes:

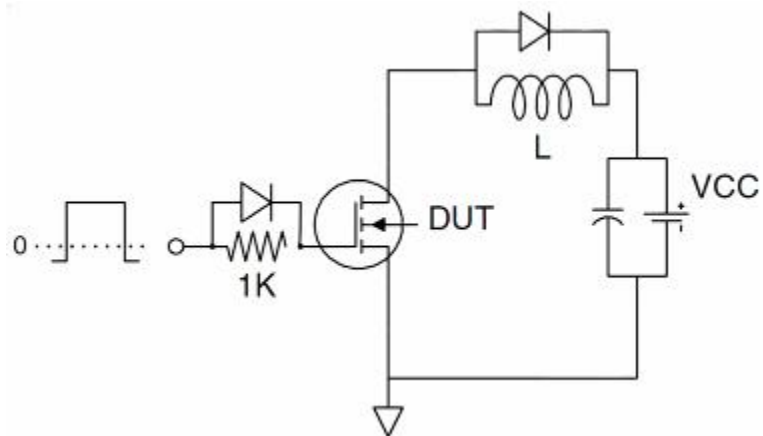
1. Surface Mounted on FR4 Board, t ≤ 10 sec.
2. Pulse Test: Pulse Width ≤ 400μs, Duty Cycle ≤ 2%.
3. EAS condition: T_J=25°C, V_{DD}=50V, V_G=10V, L=1mH, R_G=25Ω

Test Circuit

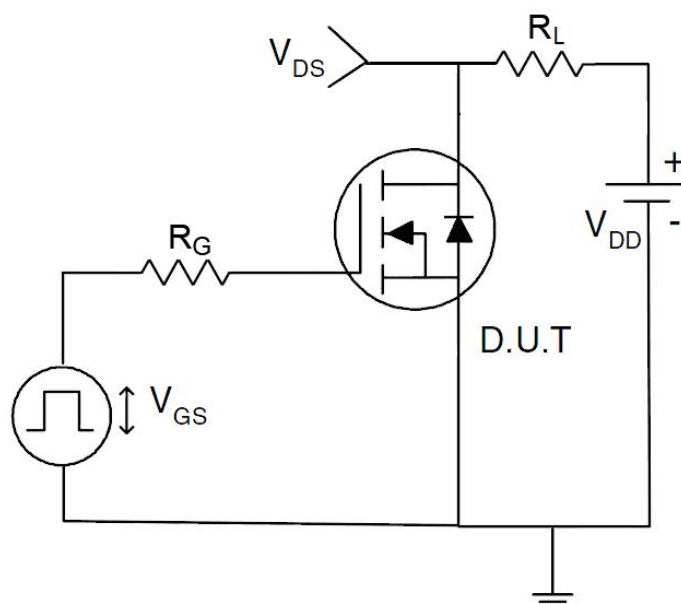
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics(Curves)

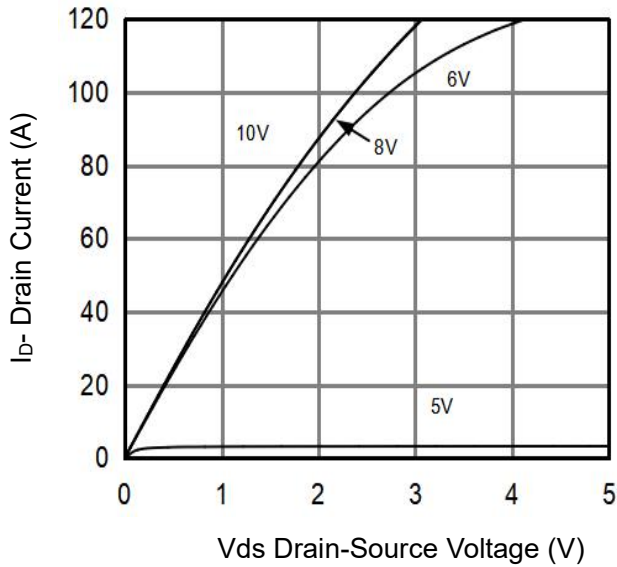


Figure 1 Output Characteristics

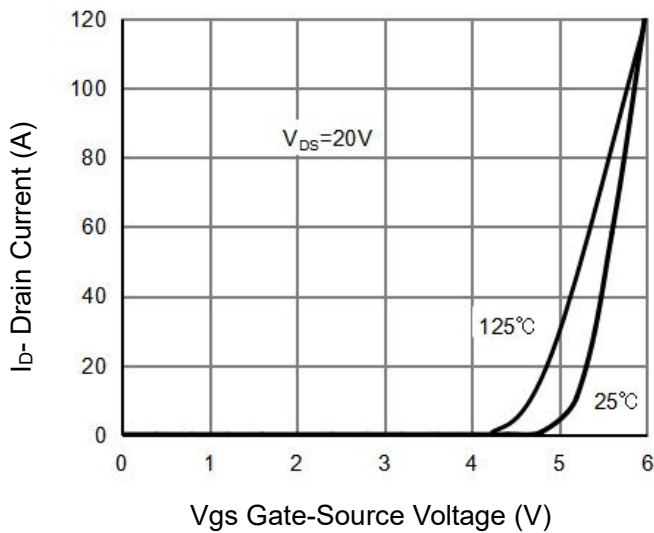


Figure 2 Transfer Characteristics

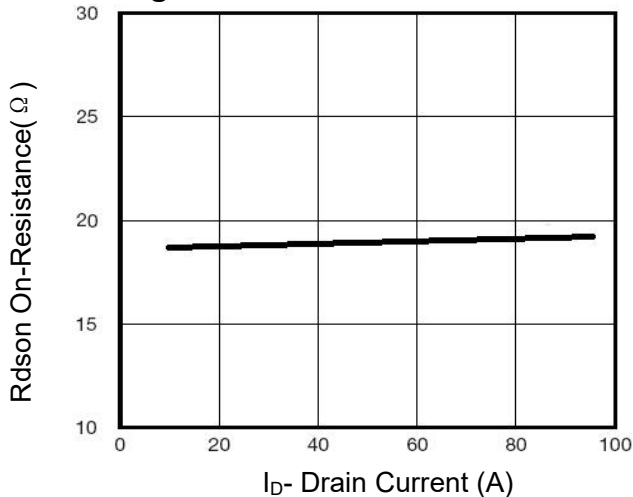


Figure 3 $R_{DS(on)}$ - Drain Current

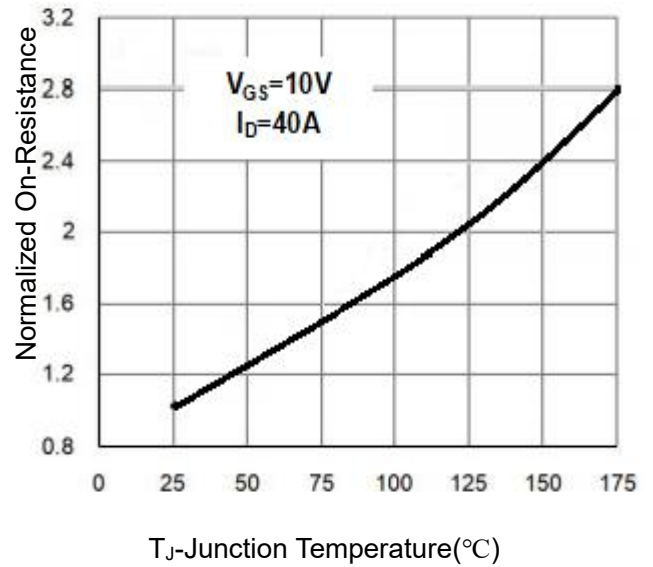


Figure 4 $R_{DS(on)}$ -Junction Temperature

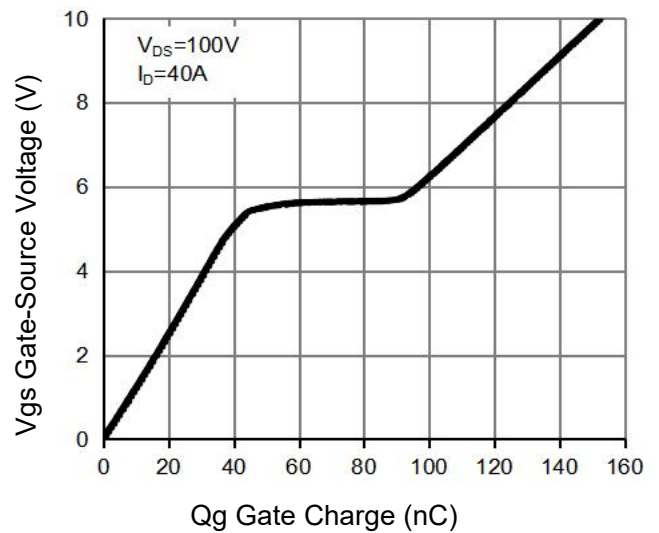


Figure 5 Gate Charge

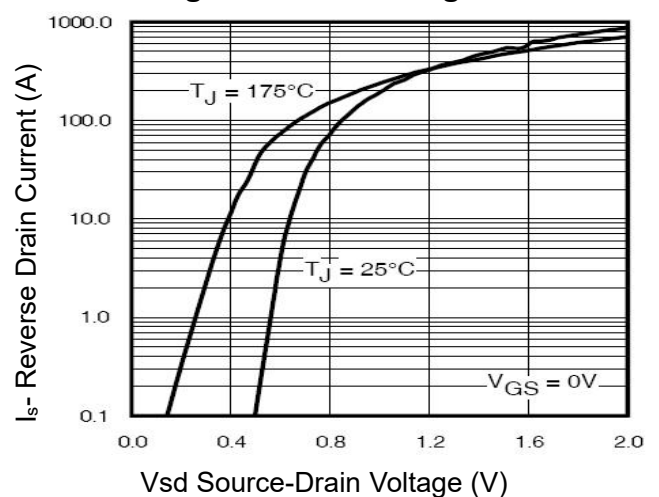


Figure 6 Source- Drain Diode Forward

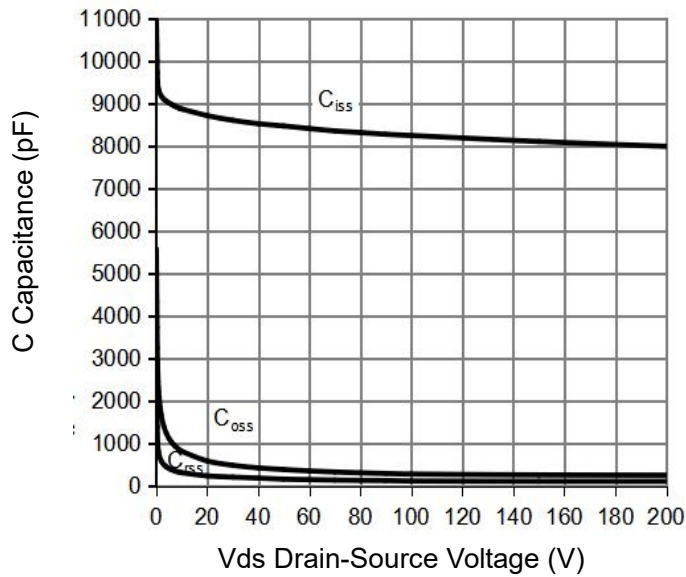


Figure 7 Capacitance vs Vds

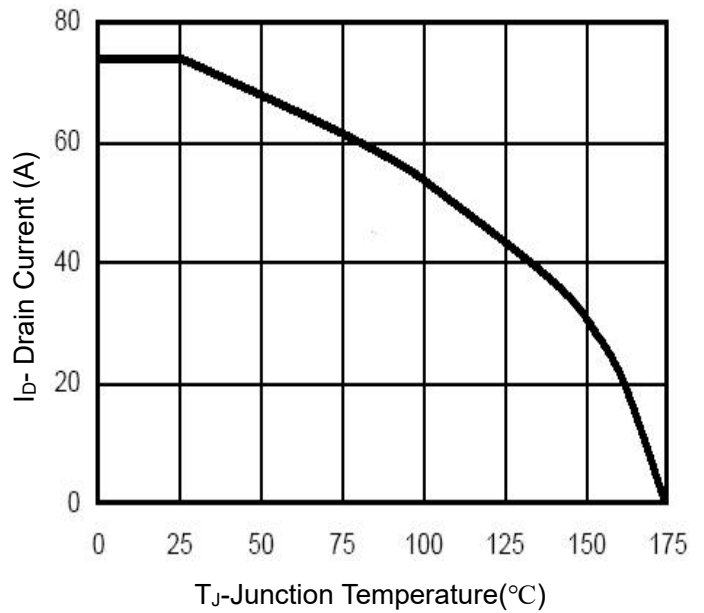


Figure 9 Current De-rating

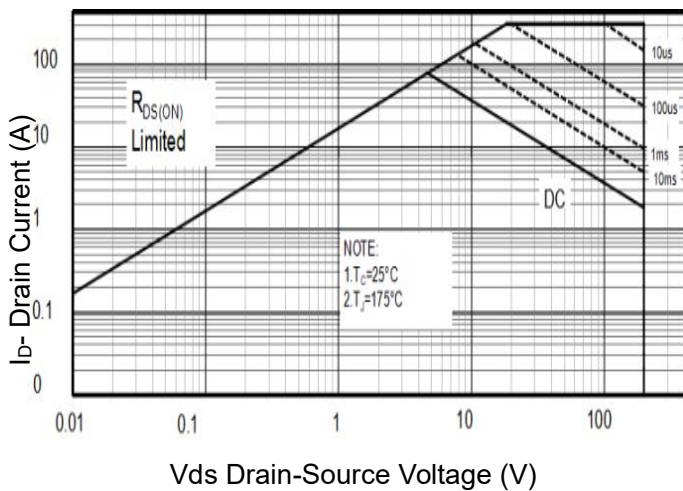


Figure 8 Safe Operation Area

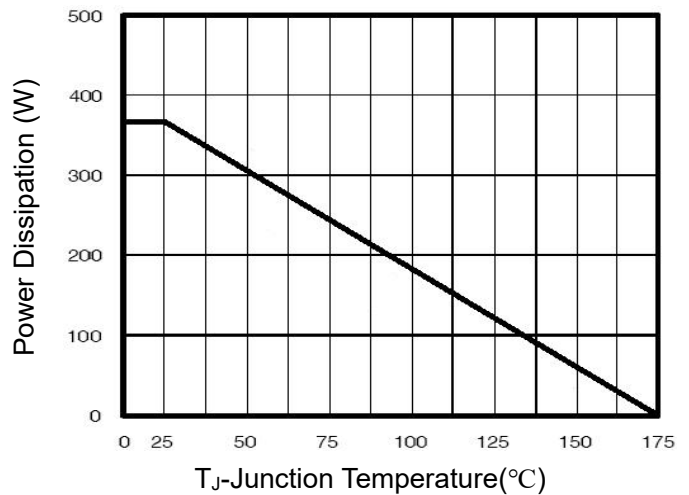


Figure 10 Power De-rating

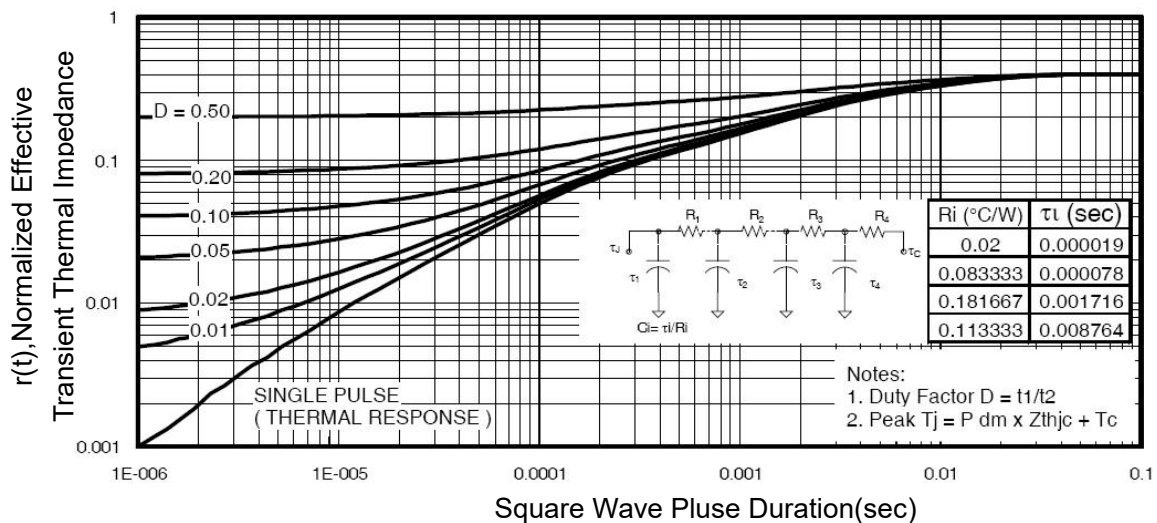
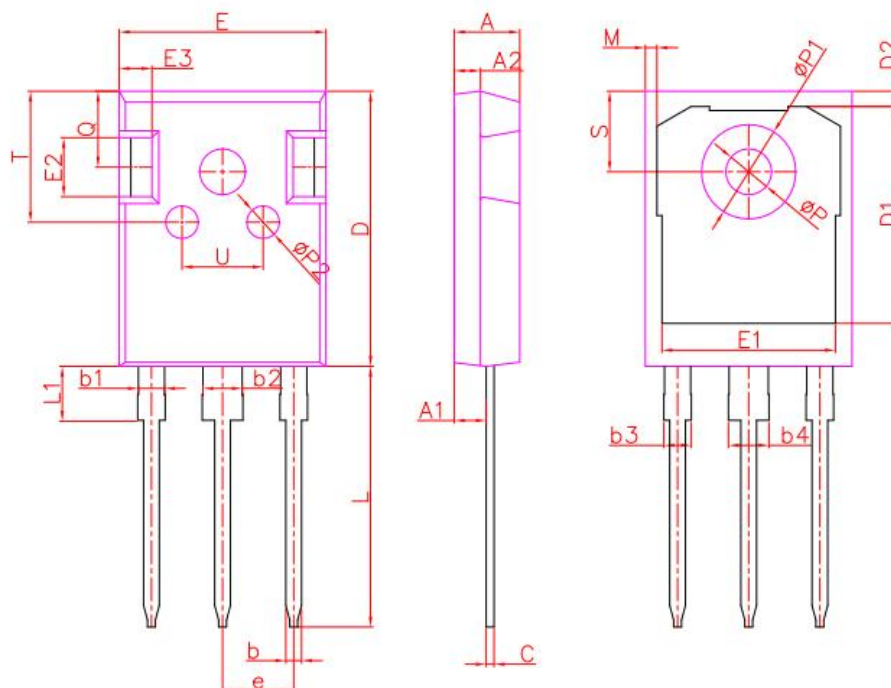


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-247-3L Package Information



TO247			
DIM.	MIN.	NOM.	MAX.
A	4.90	5.00	5.10
A1	2.31	2.432	2.51
A2	1.90	2.00	2.10
b	1.16	1.20	1.26
b1	1.96	2.00	2.06
b2	2.96	3.00	3.06
b3	—	—	2.25
b4	—	—	3.25
c	0.59	0.60	0.66
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.17	1.35
E	15.70	15.80	15.90
E1	13.10	13.26	13.50
E2	4.40	4.50	4.60
E3	2.40	2.50	2.60
e	5.436BSC		
L	19.80	19.90	20.10
L1	—	—	4.30
M	0.35	0.89	0.95
P	3.40	3.50	3.60
P1	7.00	7.20	7.40
P2	2.40	2.50	2.60
Q	5.60	5.80	6.00
S	6.05	6.15	6.25
T	9.80	10.00	10.20
U	6.00	6.20	6.40
All dimensions in millimeters			

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